

30V PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR IN SOT23

Features and Benefits

- $BV_{CEO} > -30V$
- Maximum Continuous Collector Current I_C = -1A
- 500mW power dissipation
- Complementary type:

 o FMMT549 FMMT449
 - FMMT549A N/A
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

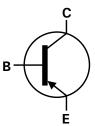
Mechanical Data

- Case: SOT23
- UL Flammability Rating 94V-0
- Case material: molded Plastic.
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

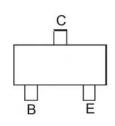
SOT23



Top View



Device Symbol



Top View Pin-Out

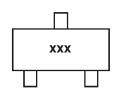
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT549TA	549	7	8	3,000
FMMT549ATA	59A	7	8	3,000

1. No purposefully added lead. Notes:

- 2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com
- 3. For Packaging Details, go to our website at http://www.diodes.com.

Marking Information



xxx = Product Type Marking Code FMMT549: xxx = 549 FMMT549A: xxx = 59A



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-35	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2	Α
Base Current	lΒ	-200	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 4)	P_{D}	500	mW
Thermal Resistance, Junction to Ambient	(Note 4)	$R_{ heta JA}$	250	°C/W
Thermal Resistance, Junction to Lead	(Note 5)	$R_{ heta JL}$	197	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage		BV _{CBO}	-35	1	-	>	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 6)		BV _{CEO}	-30	-	-	٧	$I_C = -10mA$
Emitter-Base Breakdown Voltage		BV _{EBO}	-5	-	-	٧	$I_E = -100 \mu A$
Collector Cutoff Current		I _{CBO}	1	1	-0.1	μΑ	$V_{CB} = -30V$
			-	-	-10		$V_{CB} = -30V, T_A = 100^{\circ}C$
Emitter Cutoff Current		I _{EBO}	-	-	-0.1	μΑ	$V_{EB} = -4V$
			70	200	-		$I_C = -50 \text{mA}, V_{CE} = -2V$
			80	130	-	-	$I_C = -1A$, $V_{CE} = -2V$
Static Forward Current Transfer Ratio (Note 6)		h _{FE}	40	80	-		$I_C = -2A$, $V_{CE} = -2V$
	FMMT549		100	160	300	-	$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
	FMMT549A		150	200	500	-	$I_C = -500 \text{mA}, V_{CE} = -2V$
			-	-250	-500	mV	$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	-	-500	-750	IIIV	$I_C = -2A$, $I_B = -200mA$
	FMMT549A		-	-	-300	mV	$I_C = -100 \text{mA}, I_B = -1 \text{mA}$
Base-Emitter Saturation Voltage (Note 6)		V _{BE(sat)}	-	-900	-1250	mV	$I_C = -1A$, $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 6)		$V_{BE(on)}$	1	-850	-1000	mV	$I_C = -1A$, $V_{CE} = -2V$
Output Capacitance		C_{obo}	-	-	25	рF	$V_{CB} = -10V$, $f = 1MHz$
Transition Frequency		f _T	100	-	-	MHz	$V_{CE} = -5V$, $I_{C} = -100$ mA, $f = 100$ MHz
Switching Times		t _{on}	-	50	-	ns	$I_C = -500 \text{mA}, V_{CC} = -10 \text{V}$
		t _{off}	-	300	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$

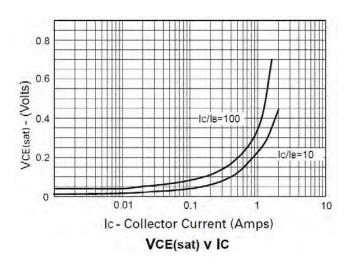
Notes:

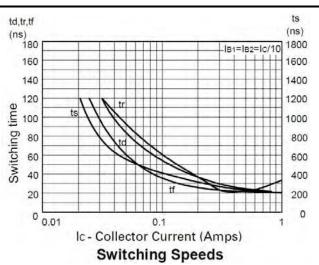
^{4.} For a device surface mounted FR4 PCB with minimum recommended pad layout; high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

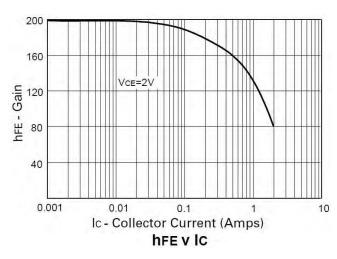
^{5.} Thermal resistance from junction to solder-point (at the end of the collector lead).
6. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%

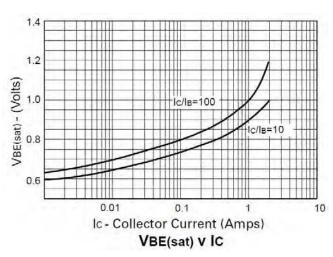


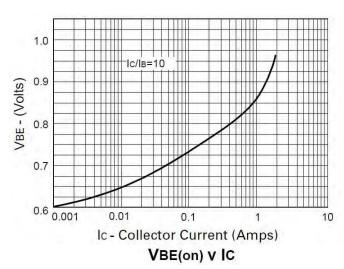
Typical Electrical Characteristics

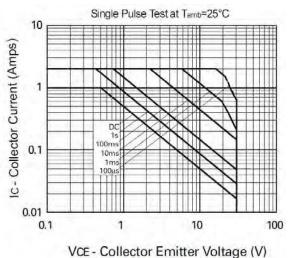






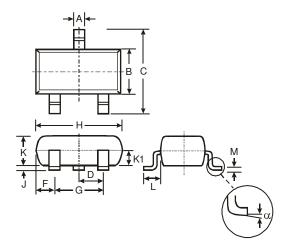






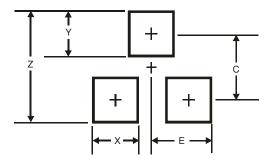


Package Outline Dimensions



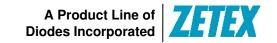
SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Υ	0.9		
С	2.0		
E	1.35		





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